AOT10N60/AOB10N60/AOTF10N60

600V,10A N-Channel MOSFET

ALPHA & OMEGA SEMICONDUCTOR

General Description

The AOT10N60 & AOB10N60 & AOTF10N60 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

For Halogen Free add "L" suffix to part number:
AOT10N60L & AOTF10N60L & AOB10N60L

Product Summary

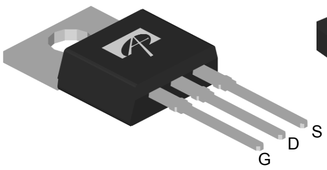
V_{DS}	700V@150℃
I_D (at V_{GS}=10V)	10A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 0.75Ω

100% UIS Tested
100% R_g Tested

RoHS Compliant

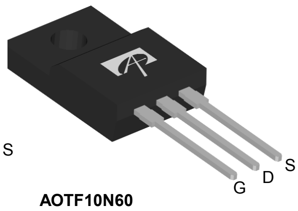
Top View

TO-220



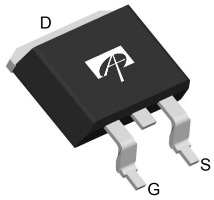
AOT10N60

TO-220F

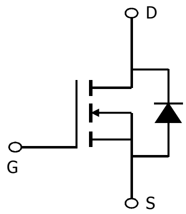


AOTF10N60

TO-263
D^2PAK



AOB10N60



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	AOT10N60/AOB10N60	AOTF10N60	Units
Drain-Source Voltage		V_{DS}	600		V
Gate-Source Voltage		V_{GS}	±30		V
Continuous Drain Current	T_C=25°C	I_D	10	10*	A
	T_C=100°C		7.2	7.2*	
Pulsed Drain Current [C]		I_{DM}	36		
Avalanche Current [C]		I_{AR}	4.4		A
Repetitive avalanche energy [C]		E_{AR}	290		mJ
Single plused avalanche energy [G]		E_{AS}	580		mJ
MOSFET dv/dt ruggedness		dv/dt	45		V/ns
Peak diode recovery dv/dt			5		
Power Dissipation [B]	T_C=25°C	P_D	250	50	W
	Derate above 25°C		2	0.4	W/ °C
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300		°C

Thermal Characteristics

Parameter	Symbol	AOT10N60/AOB10N60	AOTF10N60	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	65	65	°C/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	0.5	--	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	2.5	°C/W

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	600			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		700		
BV_{DSS} /ΔTJ	Breakdown Voltage Temperature Coefficient	I_D=250µA, V_{GS}=0V		0.65		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V			1	µA
		V_{DS}=480V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V I_D=250µA	3	4	4.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=5A		0.6	0.75	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=5A		15		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.73	1	V
I_S	Maximum Body-Diode Continuous Current				10	A
I_{SM}	Maximum Body-Diode Pulsed Current				36	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz	1100	1320	1600	pF
C_{oss}	Output Capacitance		105	130	160	pF
C_{rss}	Reverse Transfer Capacitance		7.5	9.3	11	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	3	3.8	6	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=10A		31	40	nC
Q_{gs}	Gate Source Charge			6	10	nC
Q_{gd}	Gate Drain Charge			14.4	20	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=300V, I_D=10A, R_G=25Ω		28	35	ns
t_r	Turn-On Rise Time			66	80	ns
$t_{D(off)}$	Turn-Off DelayTime			76	95	ns
t_f	Turn-Off Fall Time			64	80	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=10A,dI/dt=100A/µs,V_{DS}=100V		290	350	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=10A,dI/dt=100A/µs,V_{DS}=100V		3.9	4.7	µC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25° C.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C, Ratings are based on low frequency and duty cycles to keep initial T_J =25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. L=60mH, I_{AS}=4.4A, V_{DD}=150V, R_G=25Ω, Starting T_J=25° C

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

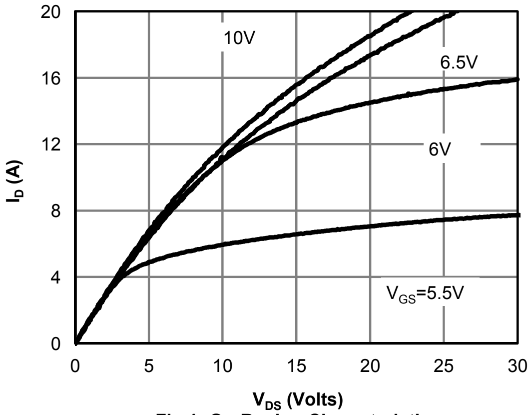


Fig 1: On-Region Characteristics

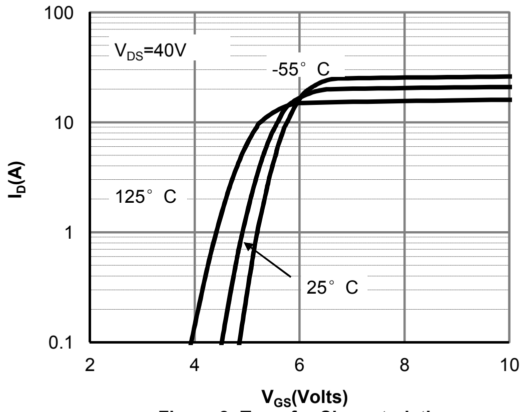


Figure 2: Transfer Characteristics

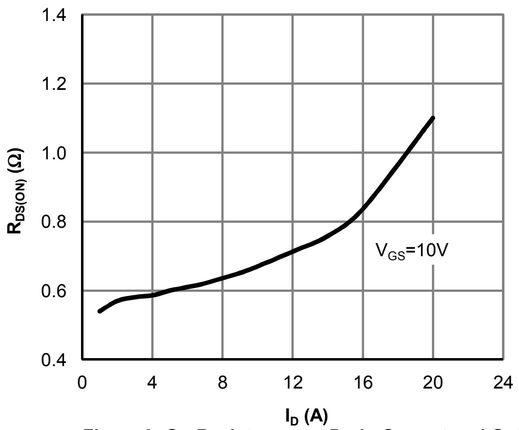


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

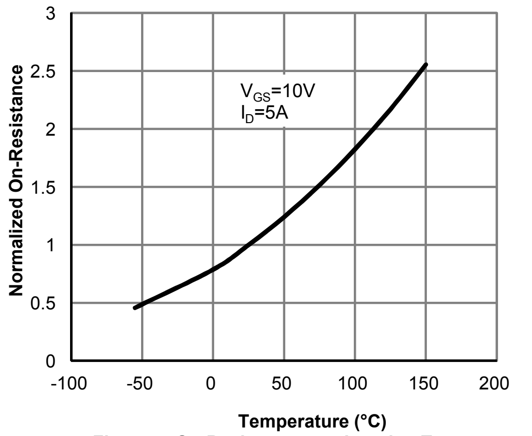


Figure 4: On-Resistance vs. Junction Temperature

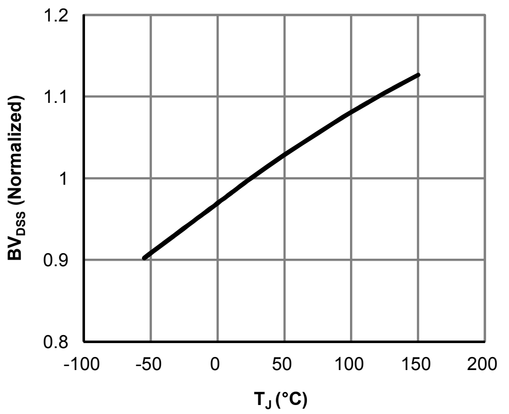


Figure 5:Break Down vs. Junction Temperature

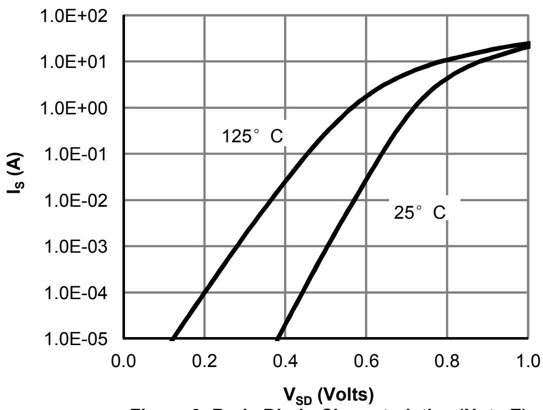


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

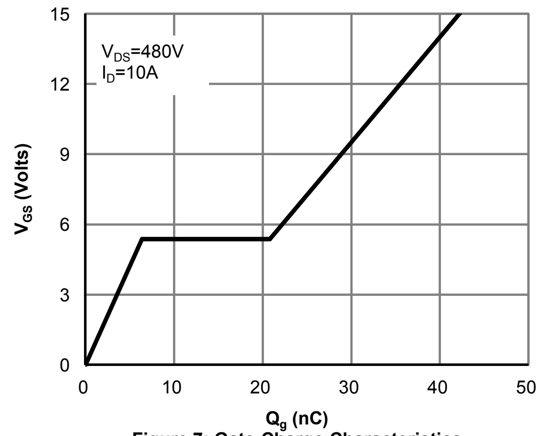


Figure 7: Gate-Charge Characteristics

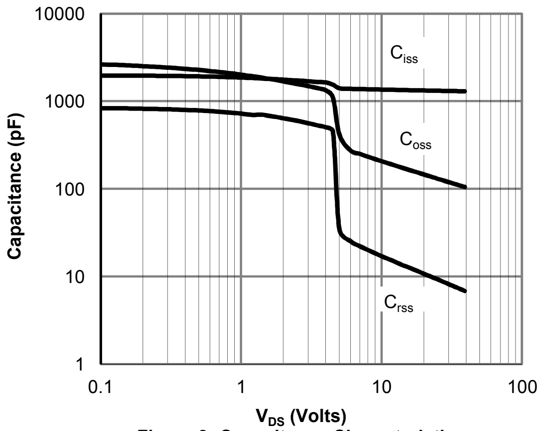


Figure 8: Capacitance Characteristics

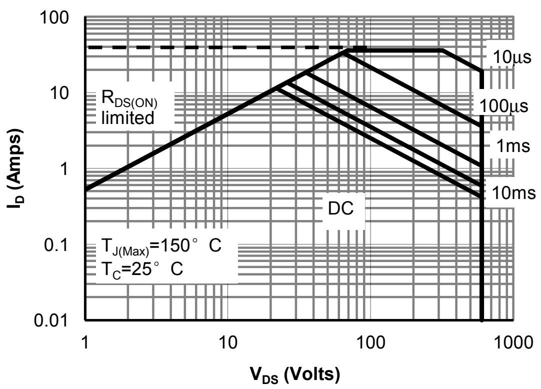


Figure 9: Maximum Forward Biased Safe Operating Area for AOT10N60/AOB10N60 (Note F)

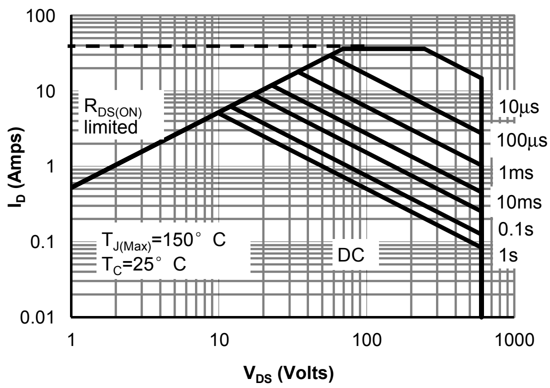


Figure 10: Maximum Forward Biased Safe Operating Area for AOTF10N60 (Note F)

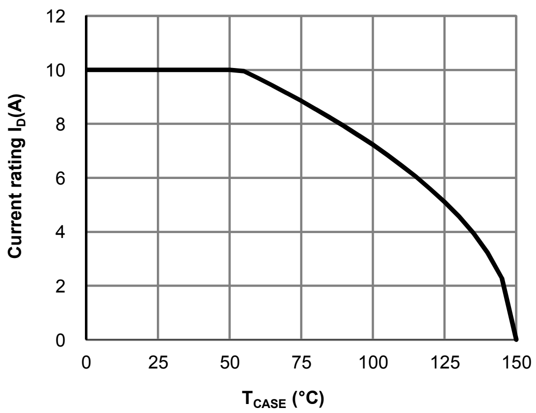


Figure 11: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

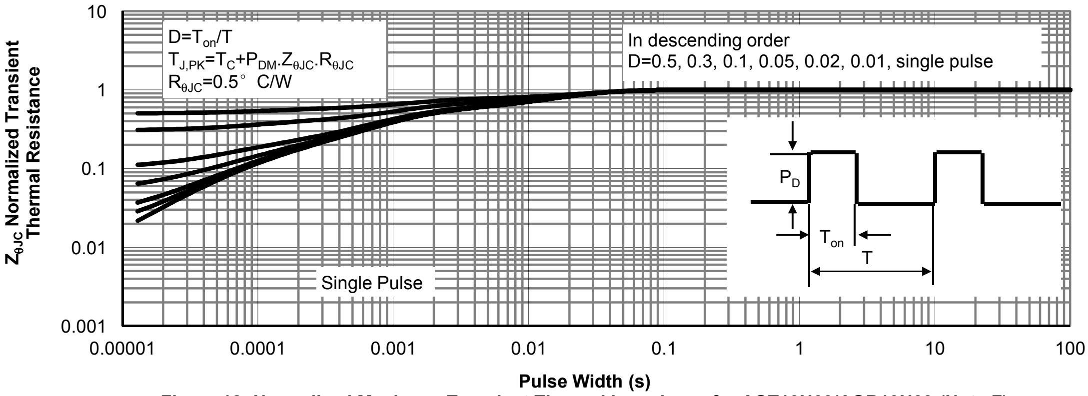


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT10N60/AOB10N60 (Note F)

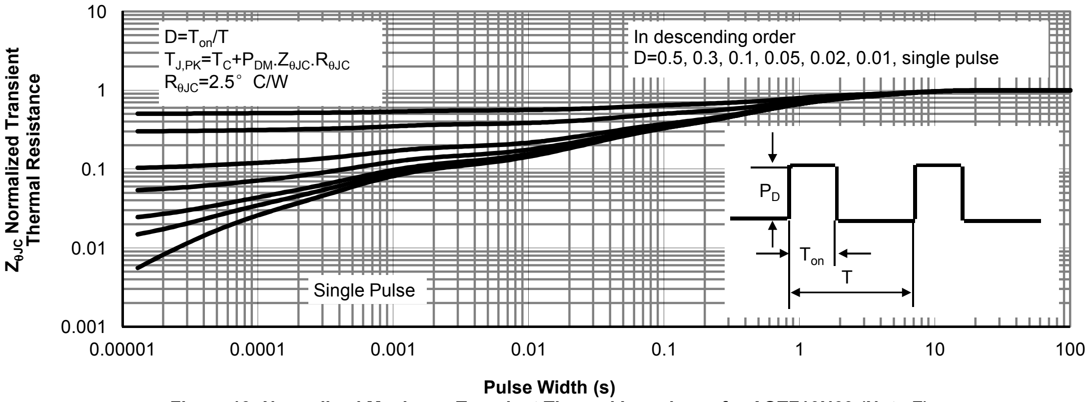
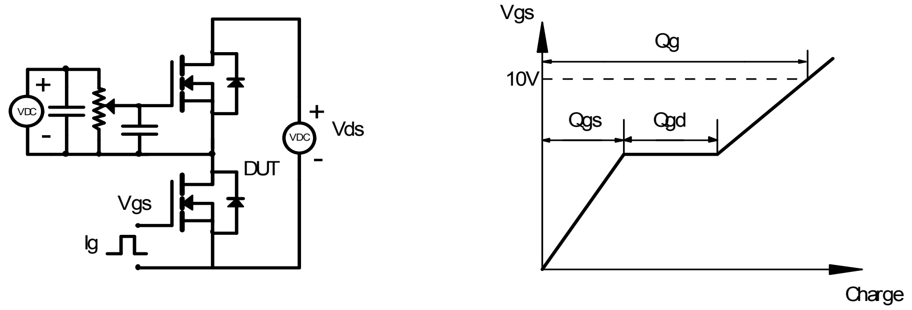
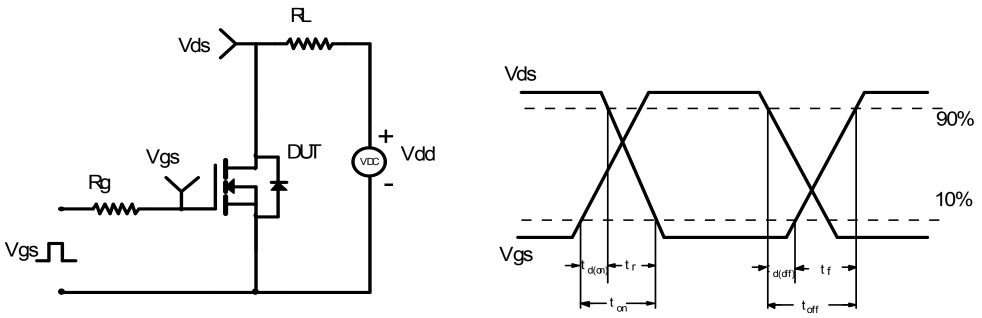


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF10N60 (Note F)

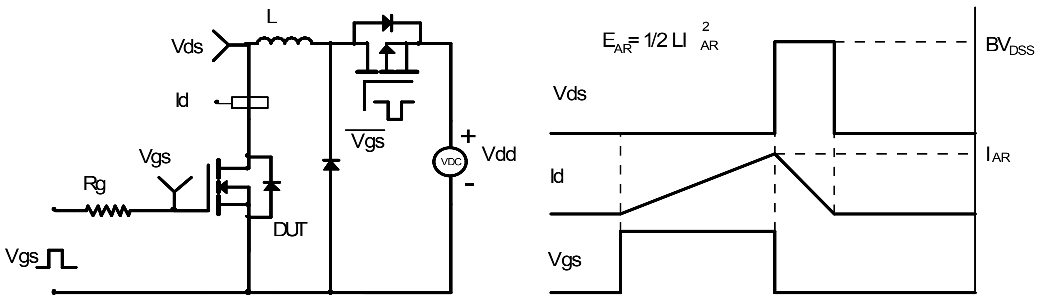
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms